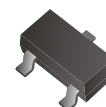


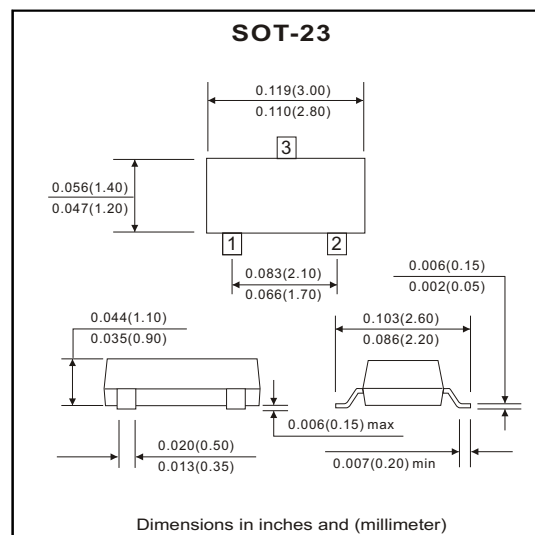
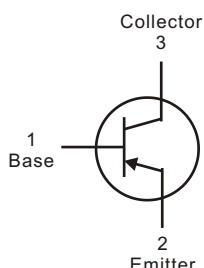
MMBT4403-G (PNP) RoHS Device



Features

-Switching transistor.

Marking: 2T



Maximum Ratings (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base voltage	V_{CBO}	-40	V
Collector-Emitter voltage	V_{CEO}	-40	V
Emitter-Base voltage	V_{EBO}	-5	V
Collector current-continuous	I_C	-0.6	A
Collector power dissipation	P_C	300	mW
Junction temperature	T_J	150	°C
Storage temperature range	T_{STG}	-55 to +150	°C

Electrical Characteristics (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ.	Max	Unit
Collector-Base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40			V
Collector-Emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-40			V
Emitter-Base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -35V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -35V, I_B = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -2V, I_C = -150mA$	100		300	
Collector-Emitter saturation voltage	$V_{CE(SAT)}$	$I_C = -150mA, I_B = -15mA$			-0.4	V
Base-Emitter saturation voltage	$V_{BE(SAT)}$	$I_C = -150mA, I_B = -15mA$			-0.95	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -20mA, f = 100MHz$	200			MHz

RATING AND CHARACTERISTIC CURVES (MMBT4403-G)

Fig. 1 Max. Power Dissipation vs. Ambient Temperature

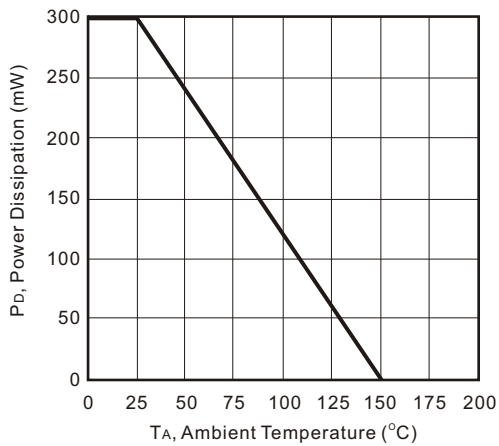


Fig. 2 Typical DC Current Gain vs. Collector Current

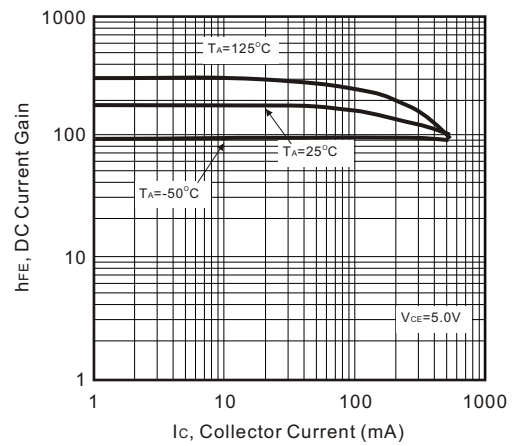


Fig. 3 Typical Capacitance

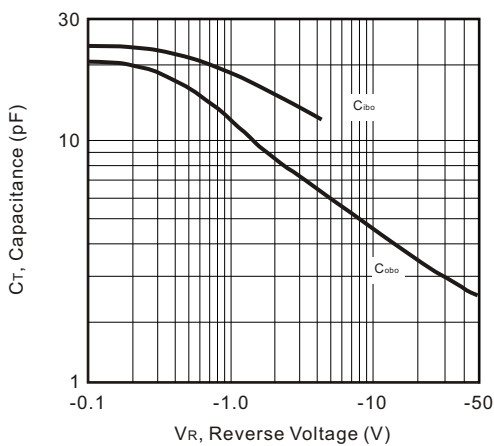


Fig. 4 Typical Collector Saturation Region

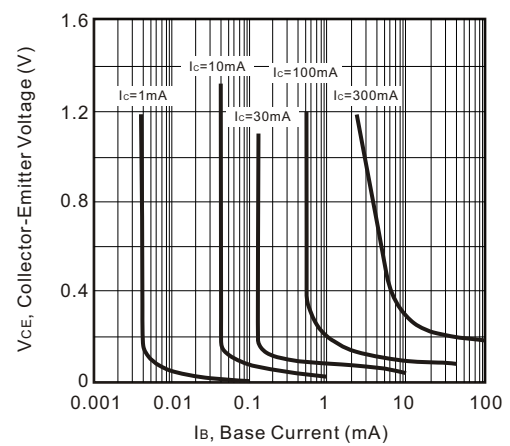


Fig. 5 Collector-Emmitter Saturation Voltage vs. Collector Current

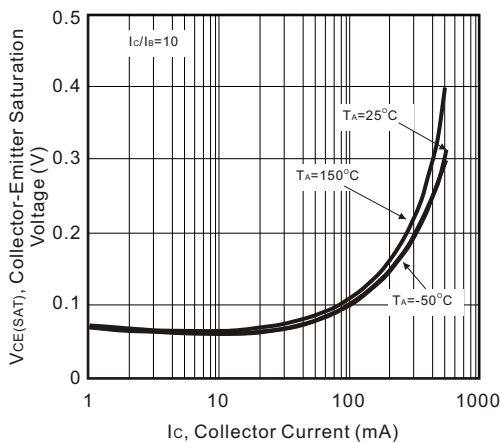


Fig. 6 Base-Emmitter Voltage vs. Collector Current

